

INFORMATION DISCLOSURE STATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) F03-354-USDiv	Application Number 10/634,836		
				Applicant(s) Hisaki KATO, et al.			
				Filing Date August 6, 2003	Group Art Unit 2822		
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
KR		H7-7182	01/10/99	Japan			YES <i>A/B5</i> NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
KR		Japanese Office Action, dated May 24, 2005, with partial English translation					
KR		NAKAMURA, et al., "Ridge-geometry InGaN multi-quantum-well-structure laser diodes", APPLIED PHYSICS LETTERS, September 2, 1996, Vol. 69, No. 10, pp. 1477-1479					
EXAMINER <i>Karen Rose</i>		DATE CONSIDERED <i>9 Feb 06</i>					
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							